







TPS62743, TPS627431

ZHCSDS4B - JUNE 2015 - REVISED MARCH 2021

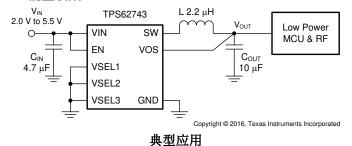
具有超低静态电流的 TPS62743 TPS627431 300/400mA 高效降压转换器

1 特性

- 输入电压范围 V_{IN}: 2.15V 至 5.5V
- 启动后的输入电压低至 2.0V
- 输出电流
 - TPS62743 300mA
 - TPS627431 400mA
- 360nA 工作静态电流
- 10µA 输出电流时的效率高达 90%
- 节能模式操作
- 可选输出电压
 - 8 个电压选项 (1.2V 至 3.3V)
- 输出电压放电
- 低输出电压纹波
- 自动转换至无纹波 100% 模式
- 射频友好型 DCS-Control™
- 总体解决方案尺寸小于 10mm²
- 小型 1.6mm × 0.9mm 8 焊球 WCSP 封装

2 应用

- 可穿戴设备
- 健身追踪器
- 智能手表
- 健康状况监控
- 低功耗蓝牙®、RF4CE、Zigbee
- 高效率、超低功耗应用
- 能量收集



3 说明

TPS62743 是一款高效降压转换器,具有典型值为 360nA 的超低静态电流。该器件经优化可搭配 2.2µH 电感和 10μF 输出电容正常工作。该器件采用 DCS-Control™ 技术,开关频率典型值为 1.2MHz。在节能 模式下,该器件可将轻负载效率向下扩展至 10 μ A 负 载电流及以下。TPS62743 提供 300mA 的输出电流。 启动后,该器件可在低至 2.0V 的输入电压下工作。因 此,可直接由单节 Li-MnO₂ 纽扣电池为器件供电。

TPS62743 提供了 8 个可编程的输出电压,可通过三 个选择引脚在 1.2V 至 3.3V 范围内进行选择。The TPS62743 经过优化,只需使用一个小型输出电容即可 获得低输出电压纹波和低噪声。一旦输入电压接近输出 电压,器件便会进入无纹波 100% 模式,以防止输出 纹波电压增大。在此工作模式下,器件会停止开关操作 并导通高侧 MOSFET。

器件信息(1)

	,,,,	
器件型号	封装	封装尺寸(标称值)
TPS62743	DSBGA (8)	1.57mm x 0.88mm
TPS627431	DSBGA (8)	1.57mm x 0.88mm

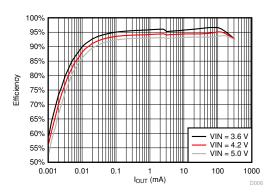




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4 Revision History

注:以前版本的页码可能与当前版本的页码不同

Changes from Revision A (May 2016) to Revision B (March 2021)	Page
• 更新了整个文档的表、图和交叉参考的编号格式。	1
Changes from Revision * (June 2015) to Revision A (May 2016)	Page
• 向数据表添加了 TPS627431 器件	1
• 添加了器件选项 TPS627431:400mA 输出电流,不同于 TPS62743 的其他输出电压	
• Added TPS627431 to 节 5	3
• Added 图 9-2	

5 Device Comparison Table

T _A	PART NUMBER	OUTPUT VOLTAGE SETTINGS (VSEL 1 - 3)	OUTPUT CURRENT	PACKAGE MARKING
- 40°C to 85°C	TPS62743	1.2 V, 1.5 V, 1.8 V, 2.1 V, 2.5 V, 2.8 V, 3.0 V, 3.3 V	300 mA	TPS743
- 40°C to 85°C	TPS627431	1.3 V, 1.4 V, 1.6 V, 1.7 V, 1.9 V, 2.0 V, 2.9 V, 3.1 V	400 mA	627431

6 Pin Configuration and Functions

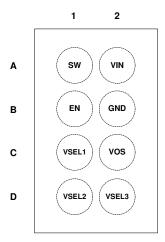


图 6-1. YFP Package 8-Pin DSBGA Top View

表 6-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO	"0	DESCRIPTION
VIN	A2	PWR	V_{IN} power supply pin. Connect the input capacitor close to this pin for best noise and voltage spike suppression. A ceramic capacitor of 4.7 μ F is required.
SW	A1	OUT	The switch pin is connected to the internal MOSFET switches. Connect the inductor to this terminal.
GND	B2	PWR	GND supply pin. Connect this pin close to the GND terminal of the input and output capacitor.
vos	C2	IN	Feedback pin for the internal feedback divider network and regulation loop. Discharges V _{OUT} when the converter is disabled. Connect this pin directly to the output capacitor with a short trace.
VSEL3	D2	IN	Output voltage selection pins. See 表 6-2 for V _{OUT} selection. These pin must be terminated. The pins can
VSEL2	D1	IN	be dynamically changed during operation.
VSEL1	C1	IN	
EN	B1	IN	High level enables the devices, low level turns the device off. The pin must be terminated.

表 6-2. Output Voltage Setting

OUTPUT VOLTAGI	SETTING V _{OUT} [V]	VSEL SETTING				
TPS62743	TPS627431	VSEL3	VSEL2	VSEL1		
1.2	1.3	0	0	0		
1.5	1.4	0	0	1		
1.8	1.6	0	1	0		
2.1	1.7	0	1	1		
2.5	1.9	1	0	0		
2.8	2.0	1	0	1		
3.0	2.9	1	1	0		
3.3	3.1	1	1	1		



7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
Pin voltage ⁽²⁾	VIN	- 0.3	6	V
	SW,	- 0.3	V _{IN} +0.3V	V
	EN, VSEL1-3	- 0.3	V _{IN} +0.3V	V
	VOS	- 0.3	3.7	V
Operating junction temperature, T _J		- 40	125	°C
Storage temperature, T _s	tg	- 65	150	°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute - maximum - rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2000	V
V _(ESD)	(ESD) Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±500	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. The human body model is a 100-pF capacitor discharged through a 1.5-k Ω resistor into each pin.

7.3 Recommended Operating Conditions

			MIN	NOM	MAX	UNIT	
V _{IN}	Supply voltage V _{IN}		2.15		5.5	V	
V _{IN}	Supply voltage V _{IN} , once started				5.5	V	
1		TPS62743 / TPS627431 5.5V ≥ VIN ≥ (VOUTnom + 0.7V) ≥ 2.15V			300		
I _{OUT}	Device output current	$5.5V \geqslant VIN \geqslant (VOUTnom + 0.7V) \geqslant 3V$			400	mA	
T_J	Operating junction temperature range				125	°C	

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⁽²⁾ All voltage values are with respect to network ground terminal GND.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.4 Thermal Information

		TPS62743	
	THERMAL METRIC(1)	YFP	UNIT
		8 PINS	
R ₀ JA	Junction-to-ambient thermal resistance	103	°C/W
R ₀ JCtop	Junction-to-case (top) thermal resistance	1.0	°C/W
R _{θ JB}	Junction-to-board thermal resistance	20	°C/W
ψ ЈТ	Junction-to-top characterization parameter	0.3	°C/W
∮ ЈВ	Junction-to-board characterization parameter	20	°C/W
R ₀ JCbot	Junction-to-case (bottom) thermal resistance	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

7.5 Electrical Characteristics

 V_{IN} = 3.6V, T_A = -40°C to 85°C typical values are at T_A = 25°C (unless otherwise noted)

P	ARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
SUPPLY					
ı	Operating quiescent	EN = V _{IN} , I _{OUT} = 0μA, V _{OUT} = 1.8V, device not switching	360	1800	nA
IQ	current	current $EN = V_{IN}$, $I_{OUT} = 0mA$, $V_{OUT} = 1.8V$, device switching	460		ΠA
I _{SD}	Shutdown current	EN = GND, shutdown current into V _{IN}	70	1000	nA
V _{TH_ UVLO+}	Undervoltage	Rising V _{IN}	2.075	2.15	V
V _{TH_UVLO} -	lockout threshold	Falling V _{IN}	1.925	2	V
INPUTS (EN, VSE	L1-3)				
V _{IH TH}	High level input threshold	$2.2V \leqslant V_{IN} \leqslant 5.5V$		1.1	V
V _{IL TH}	Low level input threshold	$2.2V \leqslant V_{IN} \leqslant 5.5V$	0.4		V
I _{IN}	Input bias Current		10	25	nA
POWER SWITCHE	ES				
_	High side MOSFET on-resistance	I _{OUT} = 50mA	0.45	1.12	0
R _{DS(ON)}	Low Side MOSFET on-resistance		0.22	0.65	Ω
	High side MOSFET	TPS62743 3.0V ≤ V _{IN} ≤ 5.5V	480 600	720	
1	switch current limit	TPS627431 3.0V ≤ V _{IN} ≤ 5.5V	590 650	800	A
I _{LIMF}	Low side MOSFET	TPS62743	600		mA
	switch current limit	TPS627431	650		
OUTPUT VOLTAG	E DISCHARGE		1	I	
R _{DSCH_VOS}	MOSFET on- resistance	EN = GND, I _{VOS} = -10mA into VOS pin	30	65	Ω
I _{IN_VOS}	Bias current into VOS pin	EN = V _{IN} , V _{OUT} = 2V	40	1010	nA

 V_{IN} = 3.6V, T_A = -40°C to 85°C typical values are at T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
AUTO 100% MODE TRA	NSITION					
V _{TH_100+}	Auto 100% Mode leave detection threshold ⁽¹⁾	Rising V _{IN} ,100% Mode is left with V _{IN} = V _{OUT} + V _{TH_100+}	150	250	350	\
V _{TH_100} -	Auto 100% Mode enter detection threshold ⁽¹⁾	Falling V _{IN} , 100% Mode is entered with V _{IN} = V _{OUT} + V _{TH_100} .	85	200	290	mV
OUTPUT						
	High side softstart switch current limit	- EN=low to high	80	150	200	mA
ILIM_softstart	Low side softstart switch current limit			150		
	Output voltage range	Output voltages are selected with pins VSEL 1 - 3	1.2		3.3	
	Output voltage	I _{OUT} = 10mA, V _{OUT} = 1.8V	-2.5	0%	2.5	V
V _{OUT}	accuracy	I _{OUT} = 100mA, V _{OUT} = 1.8V	- 2	0%	2	
	DC output voltage load regulation	V _{OUT} = 1.8V		0.001		%/mA
	DC output voltage line regulation	V_{OUT} = 1.8V, I_{OUT} = 100mA, 2.2V \leqslant V_{IN} \leqslant 5.0V		0		%/V

⁽¹⁾ V_{IN} is compared to the programmed output voltage (V_{OUT}). When $V_{IN} - V_{OUT}$ falls below V_{TH_100-} the device enters 100% Mode by turning the high side MOSFET on. The 100% Mode is exited when $V_{IN} - V_{OUT}$ exceeds V_{TH_100+} and the device starts switching. The hysteresis for the 100% Mode detection threshold $V_{TH_100+} - V_{TH_100-}$ will always be positive and will be approximately 50 mV(typ)

7.6 Timing Requirements

 $V_{IN} = 3.6V$, $T_{J} = -40$ °C to 85°C typical values are at $T_{A} = 25$ °C (unless otherwise noted)

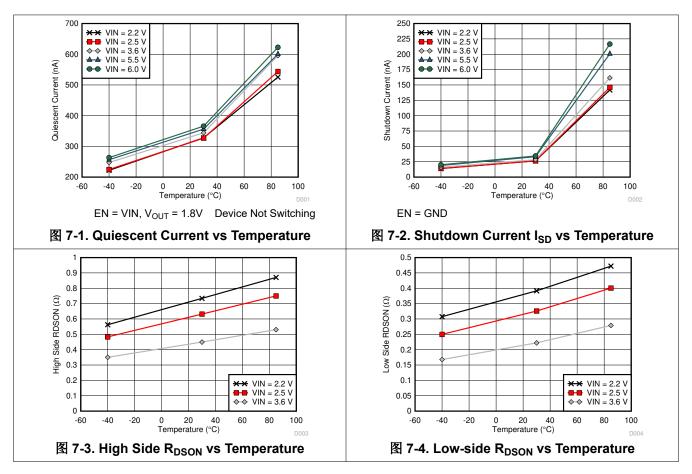
VIIN C.CV, IJ	o to oo o typica	r values are at 1 _A 20 0 (amous strict vice risted)			
PARAME	TER	TEST CONDITIONS	MIN TY	P MAX	UNIT
OUTPUT					•
t _{ONmin}	Minimum ON time	V _{OUT} = 2.0V, I _{OUT} = 0 mA	22	25	ns
t _{OFFmin}	Minimum OFF time	V _{IN} = 2.3V	ţ	50	ns
t _{Startup_delay}	Regulator start up delay time	From transition EN = low to high until device starts switching		0 2	5 ms
t _{Softstart}	Softstart time	$2.2V \leqslant V_{IN} \leqslant 5.5V$, EN = V_{IN}	70	0 120) µs

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7.7 Typical Characteristics

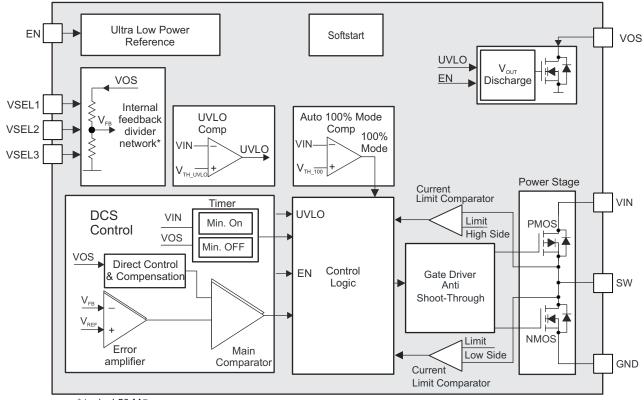


8 Detailed Description

8.1 Overview

The TPS62743 is a high frequency step down converter with ultra low quiescent current. The device operates with a quasi fixed switching frequency typically at 1.2 MHz. Using TI's DCS-Control ™ topology the device extends the high efficiency operation area down to a few microamperes of load current during Power Save Mode Operation.

8.2 Functional Block Diagram



* typical 50 MΩ

8.3 Feature Description

8.3.1 DCS-Control™

TI's DCS-Control™ (Direct Control with Seamless Transition into Power Save Mode) is an advanced regulation topology, which combines the advantages of hysteretic and voltage mode control. Characteristics of DCS-Control™ are excellent AC load regulation and transient response, low output ripple voltage and a seamless transition between PFM and PWM mode operation. DCS-Control™ includes an AC loop which senses the output voltage (VOS pin) and directly feeds the information to a fast comparator stage. This comparator sets the switching frequency, which is constant for steady state operating conditions, and provides immediate response to dynamic load changes. In order to achieve accurate DC load regulation, a voltage feedback loop is used. The internally compensated regulation network achieves fast and stable operation with small external components and low ESR capacitors.

The DCS-Control™ topology supports PWM (Pulse Width Modulation) mode for medium and high load conditions and a Power Save Mode at light loads. During PWM mode, it operates in continuous conduction mode. The switching frequency is typically 1.2 MHz with a controlled frequency variation depending on the input voltage and load current. If the load current decreases, the converter seamlessly enters Power Save Mode to maintain high efficiency down to very light loads. In Power Save Mode, the switching frequency varies linearly with the load current. Since DCS-Control™ supports both operation modes within one single building block, the transition from PWM to Power Save Mode is seamless with minimum output voltage ripple. The TPS62743 offers

both excellent DC voltage and superior load transient regulation, combined with low output voltage ripple, minimizing interference with RF circuits.

8.3.2 Power Save Mode Operation

In Power Save Mode the device operates in PFM (Pulse Frequency Modulation) that generates a single switching pulse to ramp up the inductor current and recharges the output capacitor, followed by a sleep period where most of the internal circuits are shutdown to achieve lowest operating quiescent current. During this time, the load current is supported by the output capacitor. The duration of the sleep period depends on the load current and the inductor peak current. During the sleep periods, the current consumption of TPS62743 is reduced to 360 nA. This low quiescent current consumption is achieved by an ultra low power voltage reference, an integrated high impedance feedback divider network and an optimized Power Save Mode operation.

8.3.3 Output Voltage Selection

The TPS62743 doesn't require an external resistor divider network to program the output voltage. The device integrates a high impedance feedback resistor divider network that is programmed by the pins VSEL1-3. TPS62743 supports an output voltage range from 1.2 V to 3.3 V. The output voltage is programmed according to 表 6-2. The output voltage can be changed during operation. This can be used for simple dynamic output voltage scaling.

8.3.4 Output Voltage Discharge of the Buck Converter

The device provides automatic output voltage discharge when EN is pulled low or the UVLO is triggered. The output of the buck converter is discharged over VOS. Because of this the output voltage will ramp up from zero once the device is enabled again. This is very helpful for accurate start-up sequencing.

8.3.5 Undervoltage Lockout UVLO

To avoid misoperation of the device at low input voltages, an undervoltage lockout is used. The UVLO shuts down the device at a maximum voltage level of 2.0 V. The device will start at a UVLO level of 2.15 V.

8.3.6 Short circuit protection

The TPS6274x integrates a current limit on the high side, as well on the low side MOSFETs to protect the device against overload or short circuit conditions. The peak current in the switches is monitored cycle by cycle. If the high side MOSFET current limit is reached, the high side MOSFET is turned off and the low side MOSFET is turned on until the switch current decreases below the low side MOSFET current limit. Once the low side MOSFET current limit trips, the low side MOSFET is turned off and the high side MOSFET turns on again.

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8.4 Device Functional Modes

8.4.1 Enable and Shutdown

The device is turned on with EN=high. With EN=low the device enters shutdown. This pin must be terminated.

8.4.2 Device Start-up and Softstart

The device has an internal softstart to minimize input voltage drop during start-up. This allows the operation from high impedance battery cells. Once the device is enabled the device starts switching after a typical delay time of 10ms. Then the softstart time of typical 700 µs begins with a reduced current limit of typical 150 mA. When this time passed by the device enters full current limit operation. This allows a smooth start-up and the device can start into full load current. Furthermore, larger output capacitors impact the start-up behaviour of the DC/DC converter. Especially when the output voltage does not reach its nominal value after the typical soft-start time of 700 µs, has passed.

8.4.3 Automatic Transition Into No Ripple 100% Mode

Once the input voltage comes close to the output voltage, the DC/DC converter stops switching and enters 100% duty cycle operation. It connects the output V_{OUT} via the inductor and the internal high side MOSFET switch to the input VIN, once the input voltage V_{IN} falls below the 100% mode enter threshold, V_{TH_100-} . The DC/DC regulator is turned off, switching stops and therefore no output voltage ripple is generated. Since the output is connected to the input, the output voltage follows the input voltage minus the voltage drop across the internal high side switch and the inductor. Once the input voltage increases and trips the 100% mode exit threshold, V_{TH_100+} , the DC/DC regulator turns on and starts switching again. See 8-1 and 100% Mode Entry and Leave Operation $I_{OUT} = 30$ mA.

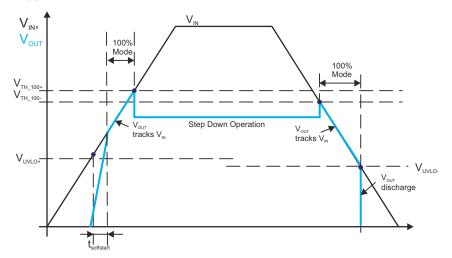


图 8-1. Automatic Transition into 100% Mode



9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The TPS62743 is a high efficiency step down converter with ultra low quiescent current of typically 360 nA. The device operates with a tiny 2.2-µH inductor and 10-µF output capacitor over the entire recommended operation range. A dedicated measurement set-up is required for the light load efficiency measurement and device quiescent current due to the operation in the sub microampere range. In this range any leakage current in the measurement set-up will impact the measurement results.

9.2 Typical Application

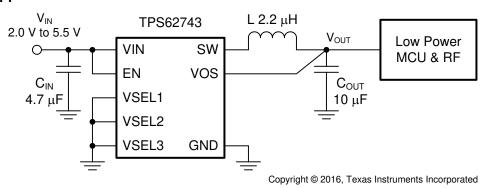


图 9-1. TPS62743 Typical Application Circuit

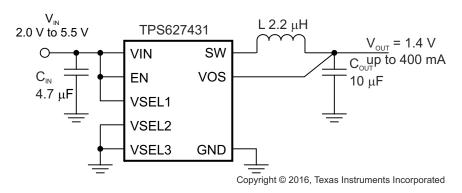


图 9-2. TPS627431 Typical Application Circuit

9.2.1 Design Requirements

The TPS62743 is a highly integrated DC/DC converter. The output voltage is set via a VSEL pin interface. The design guideline provides a component selection to operate the device within the recommended operating conditions.

表 9-1 shows the list of components for the Application Characteristic Curves.



表 9-1. Compone	ents for Application	on Characteristic Curves
----------------	----------------------	--------------------------

Reference	Description	Value	Manufacturer
TPS62743	360nA lq step down converter		Texas Instruments
CIN	Ceramic capacitor, GRM155R61C475ME15	4.7 μF	Murata
COUT	Ceramic capacitor, GRM155R60J106ME11	10 μF	Murata
L	Inductor DFE201610C	2.2 µH	Toko

9.2.2 Detailed Design Procedure

The first step in the design procedure is the selection of the output filter components. To simplify this process, 表 9-2 outlines possible inductor and capacitor value combinations.

表 9-2. Recommended LC Output Filter Combinations

Inductor Value	Output Capacitor Value [µF] ⁽¹⁾									
[µH] ⁽²⁾	4.7µF	10μF	22μF	47μF	100μF					
2.2	√	√ (3)	√	√						

- (1) Capacitance tolerance and bias voltage de-rating is anticipated. The effective capacitance varies by +20% and -50%.
- (2) Inductor tolerance and current de-rating is anticipated. The effective inductance can vary by 20% and -30%.
- (3) Typical application configuration. Other check marks indicate alternative filter combinations.

9.2.2.1 Inductor Selection

The inductor value affects the peak-to-peak ripple current, the PWM-to-PFM transition point, the output voltage ripple and the efficiency. The selected inductor has to be rated for its DC resistance and saturation current. The inductor ripple current ($^{\Delta}$ I_L) decreases with higher inductance and increases with higher V_{IN} or V_{OUT} and can be estimated according to $^{\pm}$ 71.

方程式 2 calculates the maximum inductor current under static load conditions. The saturation current of the inductor should be rated higher than the maximum inductor current, as calculated with 方程式 2. This is recommended because during a heavy load transient the inductor current rises above the calculated value. A more conservative way is to select the inductor saturation current according to the high-side MOSFET switch current limit, I_{LIMF}.

$$\Delta I_{L} = Vout \times \frac{1 - \frac{Vout}{Vin}}{L \times f}$$
 (1)

$$I_{Lmax} = I_{outmax} + \frac{\Delta I_L}{2}$$
 (2)

where

- f = Switching Frequency
- L = Inductor Value
- ∆ I_I = Peak to Peak inductor ripple current
- I_{Lmax} = Maximum Inductor current

表 9-3 shows a list of possible inductors.

表 9-3. List of Possible Inductors

INDUCTANCE [µH]	DIMENSIONS [mm³]	INDUCTOR TYPE	Isat/DCR	SUPPLIER ⁽¹⁾	Comment
2.2	2.0 x 1.6 x 1.0	DFE201610C	1.4 A/170 m Ω	TOKO	Efficiency plot
2.2	2.0 × 1.25 × 1.0	MIPSZ2012D 2R2	0.7 A/230 m Ω	FDK	Efficiency vs Load Current; V _{OUT} =
2.2	2.0 x 1.2 x 1.0	744 797 752 22	0.7 A/200 m Ω	Würth Elektronik	1.8 V
2.2	1.6 x 0.8 x 0.8	MDT1608- CH2R2M	0.7 A/300 m Ω	TOKO	

(1) See Third-party Products Disclaimer

9.2.2.2 Output Capacitor Selection

The DCS-Control™ scheme of the TPS62743 allows the use of tiny ceramic capacitors. Ceramic capacitors with low ESR values have the lowest output voltage ripple and are recommended. The output capacitor requires either an X7R or X5R dielectric. At light load currents, the converter operates in Power Save Mode and the output voltage ripple is dependent on the output capacitor value. A larger output capacitors can be used reducing the output voltage ripple. The leakage current of the output capacitor adds to the overall quiescent current.

9.2.2.3 Input Capacitor Selection

Because the buck converter has a pulsating input current, a low ESR input capacitor is required for best input voltage filtering to minimize input voltage spikes. For most applications a 4.7- μ F input capacitor is sufficient. When operating from a high impedance source, like a coin cell a larger input buffer capacitor ≥ 10 uF is recommended avoiding voltage drops during start-up and load transients. The input capacitor can be increased without any limit for better input voltage filtering. The leakage current of the input capacitor adds to the overall quiescent current. $\frac{1}{2}$ 9-4 shows a selection of input and output capacitors.

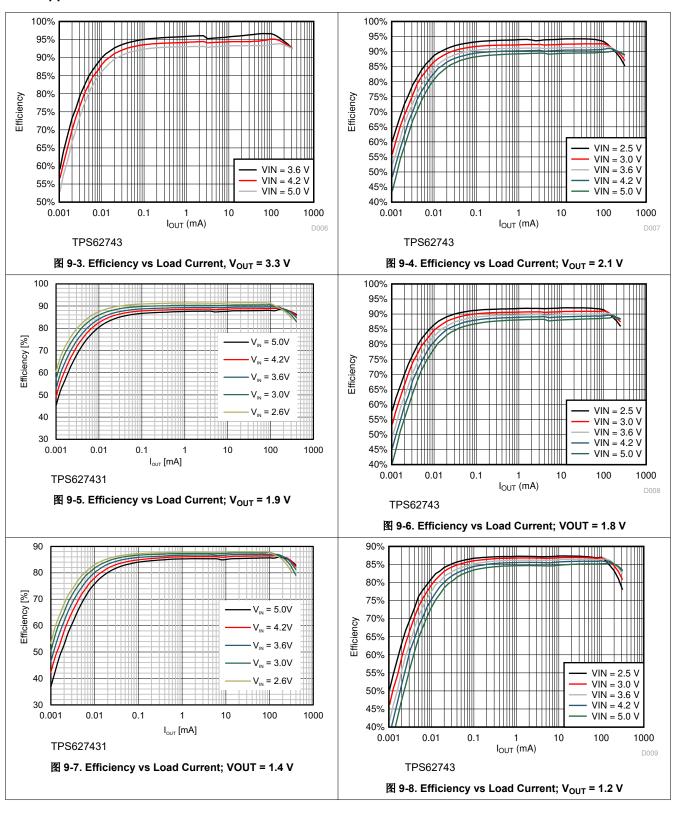
表 9-4. List of Possible Capacitors⁽¹⁾

CAPACITANCE [µ F]	SIZE	CAPACITOR TYPE	SUPPLIER		
4.7	0402	GRM155R61C475ME15	Murata		
10	0402	GRM155R60J106ME11	Murata		

(1) See Third-party Products Disclaimer

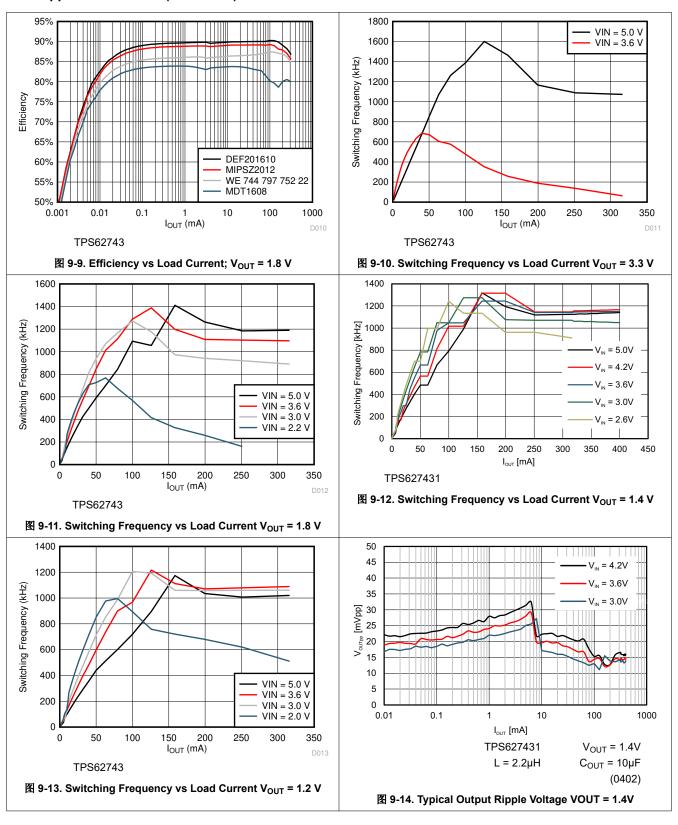


9.2.3 Application Curves



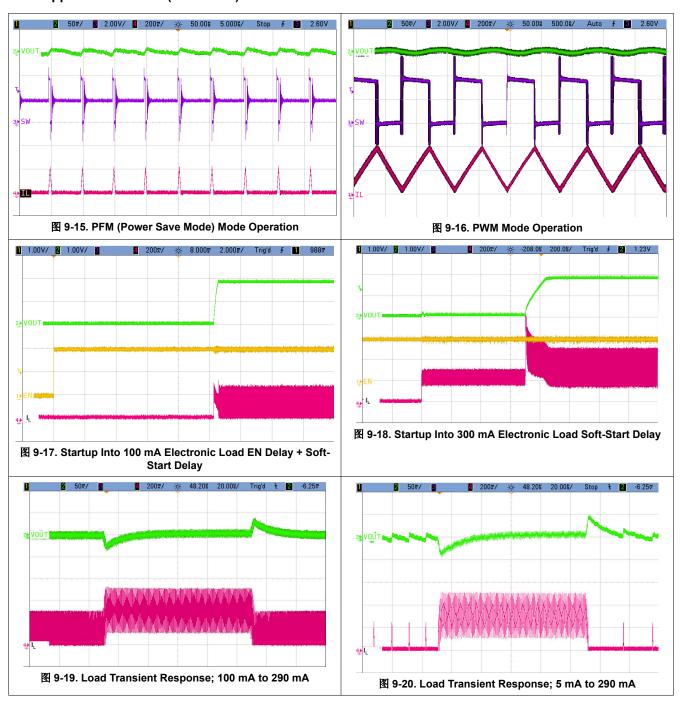


9.2.3 Application Curves (continued)

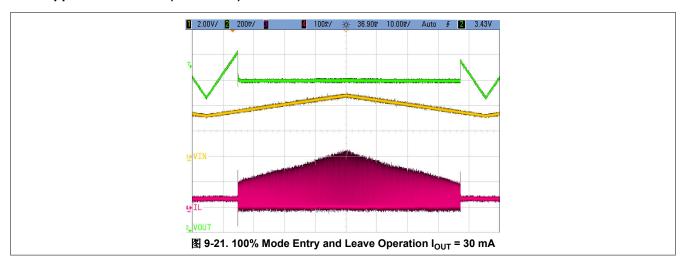




9.2.3 Application Curves (continued)



9.2.3 Application Curves (continued)



9.3 System Example

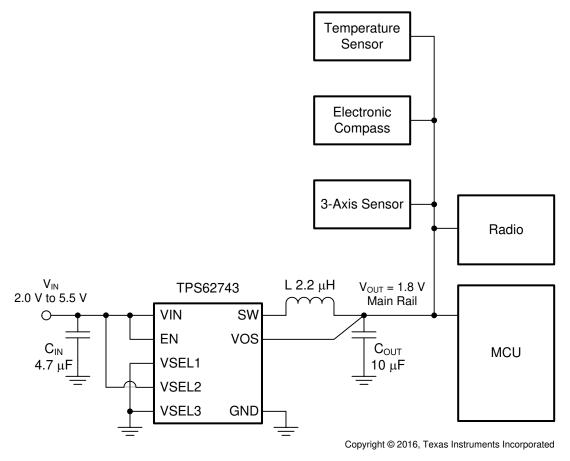


图 9-22. Example Of Implementation In A Master MCU Based System



10 Power Supply Recommendations

The power supply must provide a current rating according to the supply voltage, output voltage and output current of the TPS62743.

11 Layout

11.1 Layout Guidelines

- As for all switching power supplies, the layout is an important step in the design. Care must be taken in board layout to get the specified performance.
- It is critical to provide a low inductance, impedance ground path. Therefore, use wide and short traces for the main current paths.
- The input capacitor should be placed as close as possible to the IC pins VIN and GND. This is the most critical component placement.
- The V_{OS} line is a sensitive high impedance line and should be connected to the output capacitor and routed away from noisy components and traces (e.g. SW line) or other noise sources.

11.2 Layout Example

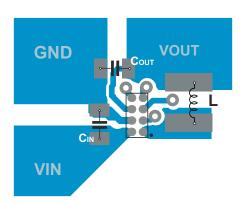


图 11-1. Recommended PCB Layout

12 Device and Documentation Support

12.1 Device Support

12.1.1 第三方产品免责声明

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12.3 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料,可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

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ESD 的损坏小至导致微小的性能降级,大至整个器件故障。精密的集成电路可能更容易受到损坏,这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

12.6 术语表

TI术语表本术语表列出并解释了术语、首字母缩略词和定义。

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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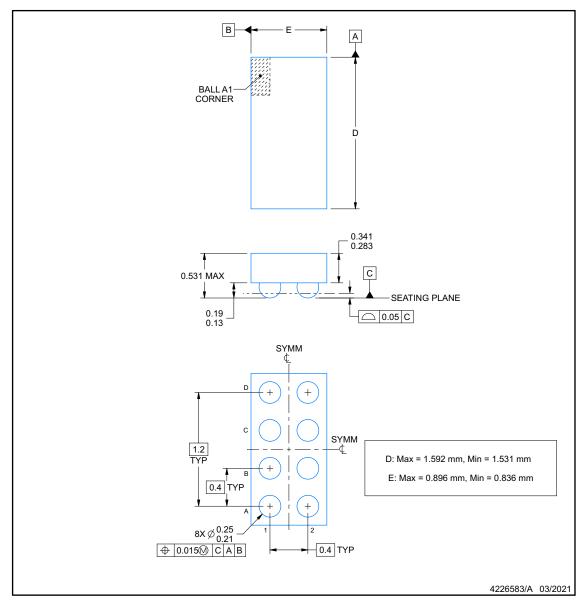


YFP0008-C01

PACKAGE OUTLINE

DSBGA - 0.531 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.



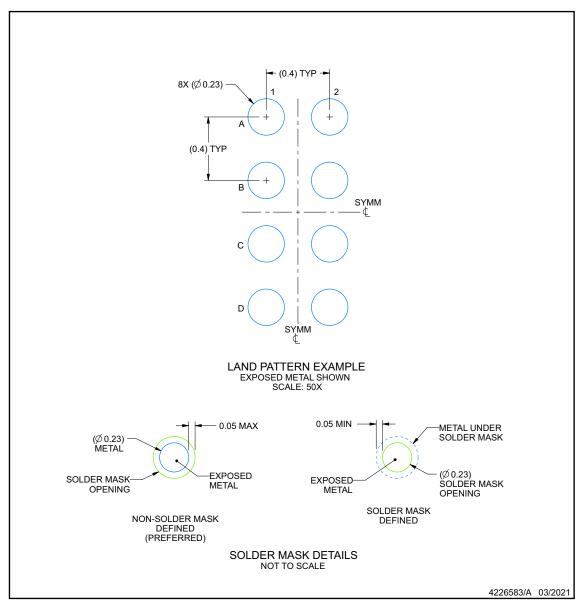


EXAMPLE BOARD LAYOUT

YFP0008-C01

DSBGA - 0.531 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. See Texas Instruments Literature No. SNVA009 (www.ti.com/lit/snva009).



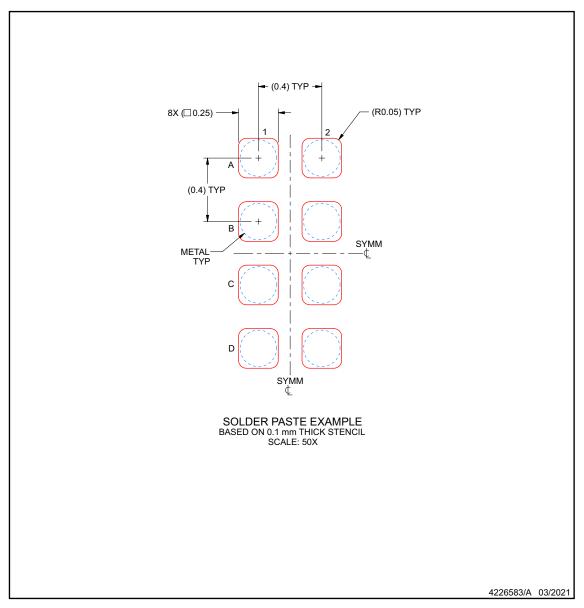


EXAMPLE STENCIL DESIGN

YFP0008-C01

DSBGA - 0.531 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.





PACKAGE OPTION ADDENDUM

12-Mar-2021

PACKAGING INFORMATION

www.ti.com

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPS627431YFPR	ACTIVE	DSBGA	YFP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	627431	Samples
TPS627431YFPT	ACTIVE	DSBGA	YFP	8	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	627431	Samples
TPS62743YFPR	ACTIVE	DSBGA	YFP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	TPS743	Samples
TPS62743YFPT	ACTIVE	DSBGA	YFP	8	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	TPS743	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

12-Mar-2021

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PACKAGE MATERIALS INFORMATION

www.ti.com 19-Jun-2024

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS627431YFPR	DSBGA	YFP	8	3000	180.0	8.4	0.98	1.68	0.59	4.0	8.0	Q1
TPS627431YFPT	DSBGA	YFP	8	250	180.0	8.4	0.98	1.68	0.59	4.0	8.0	Q1
TPS62743YFPR	DSBGA	YFP	8	3000	180.0	8.4	0.98	1.68	0.59	4.0	8.0	Q1
TPS62743YFPT	DSBGA	YFP	8	250	180.0	8.4	0.98	1.68	0.59	4.0	8.0	Q1



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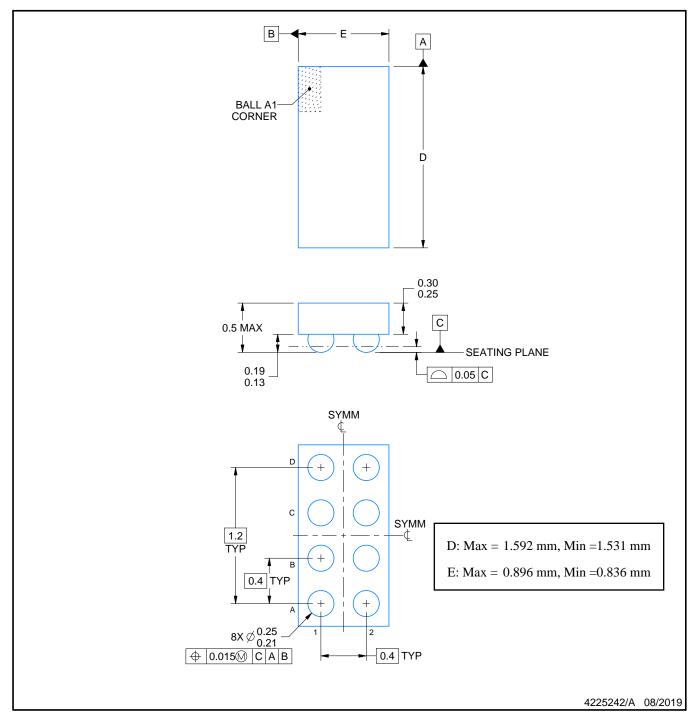


*All dimensions are nominal

7 till dillitoriolorio di o riorrillital							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS627431YFPR	DSBGA	YFP	8	3000	182.0	182.0	20.0
TPS627431YFPT	DSBGA	YFP	8	250	182.0	182.0	20.0
TPS62743YFPR	DSBGA	YFP	8	3000	182.0	182.0	20.0
TPS62743YFPT	DSBGA	YFP	8	250	182.0	182.0	20.0



DIE SIZE BALL GRID ARRAY



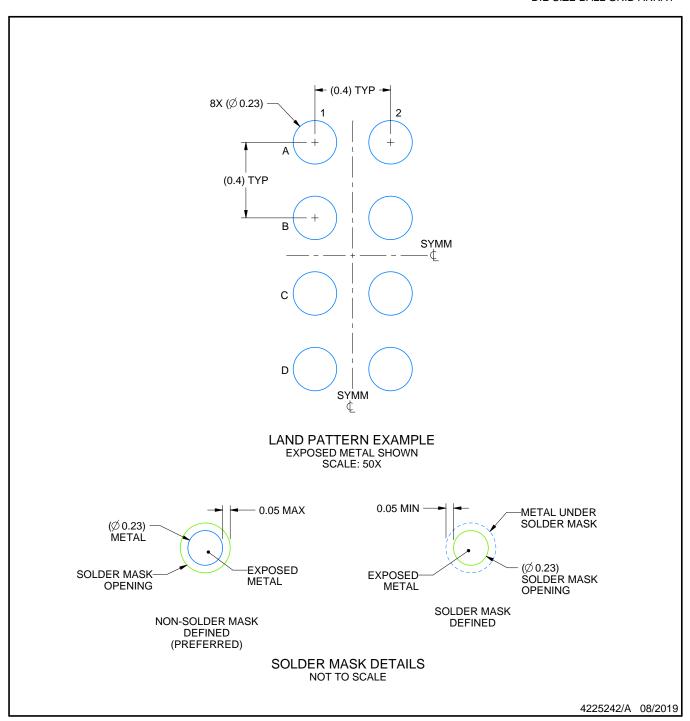
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

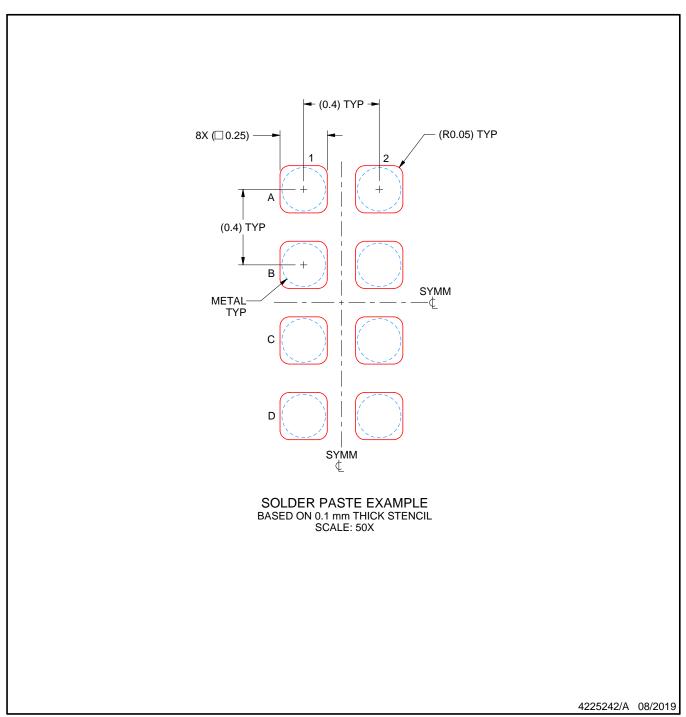


NOTES: (continued)

Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. See Texas Instruments Literature No. SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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